Dedicated to the memory of Prof. M. Sheinkman effect of ultrasonic treatment on the defect structure of the Si-SiO2 system
Kropman, Daniel; Dolgov, Sergei; Onufrijevs, Pavels; Dauksta, Edvins Gettering and Defect Engineering in Semiconductor Technology XV 2014 / p. 352-357 : ill https://doi.org/10.4028/www.scientific.net/SSP.205-206.352 Conference proceedings at Scopus Article at Scopus Conference proceedings at WOS Article at WOS

Effect of ultrasonic treatment on the defect structure of the Si-SiO2 system
Kropman, Daniel; Seeman, Viktor; Dolgov, Sergei; Medvids, Arturs Physica Status Solidi (C) Current Topics in Solid State Physics 2016 / p. 793 - 797 https://doi.org/10.1002/pssc.201600052 Journal metrics at Scopus Article at Scopus Article at WOS

Hydrogen interaction with point defects in the Si-SiO2 structures and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Abru, Uno; Medvid, A. Solid state phenomena 2008 / p. 345-350 https://www.scientific.net/SSP.131-133.345

Impurity interaction with point defects in the Si-SiO2 structures and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Medvid, A. Materials science and engineering : B 2006 / p. 222-226 : ill https://www.sciencedirect.com/science/article/pii/S0921510706004375

Interaction of point defects with impurities in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; Kärner, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, C. A. The 9th International Conference on Global Research and Education : August 9-12, 2010, Riga : digest 2010 / p. 231-233 https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564

Interaction of point defects with impurities in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, Tiit; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos; Misiuk, Andrzej Solid state phenomena 2011 / p. 263-266 https://www.sciencedirect.com/science/article/pii/S0040609009014564

Interaction of point defects with impurities in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; Kärner, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos Physica status solidi (c) 2011 / p. 694-696 : ill https://www.sciencedirect.com/science/article/pii/S0040609009014564

Interaction of point defects with impurities in the Si-SiO2 system and its influence on the properties of the interface
Kropman, Daniel; **Mellikov, Enn**; **Öpik, Andres**; **Lott, Kalju**; Kärner, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A.; Skroupa, W.; Prucnal, S.; Rebohle, L.; Zvyagin, S.; Cizmar, E.; Ozerov, M.; Wosnitsa, J. Thin solid films 2010 / 9, p. 2374-2376 https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564

Interaction of point defects with impurities in the Si-SiO2 system and its influence on the properties of the interface
Kropman, Daniel; **Mellikov, Enn**; **Lott, Kalju**; Kärner, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A.; Skroupa, W.; Prucnal, S.; Zvyagin, S.; Cizmar, E.; Ozerov, M.; Wosnitsa, J. Solid state phenomena 2010 / p. 145-148 : ill https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564

Interaktsioon punktdefektide ja lisandite vahel süsteemis Si-SiO2 ja nende mõju piirpinna omadustele : [ettekande sisukokkuvõte]
Kropman, Daniel; Kärner, T.; Heinmaa, I. Eesti Füüsika Seltsi aastaraamat 2008 2009 / lk. 119-120

Low-K factor of SiO2 layer on Si irradiated by YAG:Nd laser
Medvid, A.; Onufrijevs, Pavels; **Mellikov, Enn**; **Kropman, Daniel**; Muktepavela, F.; Bakradze, G. Journal of non-crystalline solids 2007 / p. 703-707 : ill https://www.sciencedirect.com/science/article/pii/S0022309306014116

Point defects interaction with extended defects and impurities and its influence on the Si-SiO2 system properties
Kropman, Daniel; Arbu, Uno; Kärner, T.; Ugaste, Ülo; **Mellikov, Enn**; **Kauk, Marit**; Heinmaa, I.; **Samoson, Ago**; Medvid, A. Gettering and defect engineering in semiconductor technology. XI 2005 / p. 333-338 : ill https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO_2_System_Properties

Strain relaxation mechanism in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; **Öpik, Andres**; **Lott, Kalju**; **Volobujeva, Olga**; Kärner, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A. Radiation Interaction with Materials and its use in Technologies : Kaunas, 24-27.09.2008 2008 / p. 204-207 https://www.sciencedirect.com/science/article/pii/S0921452609010321

Strain relaxation mechanism in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; **Öpik, Andres**; **Lott, Kalju**; **Volobujeva, Olga**; Kärner, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A. Physica B : condensed matter 2009 / 23/24, p. 5153-5155 : ill

Stress relaxation mechanism by strain in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksta, Edvins Solid state

phenomena 2011 / p. 259-262 https://globaljournals.org/GJSFR_Volume17/1-Stresses-Relaxation-Mechanism.pdf

Stress relaxation mechanism by strain in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; Seeman, Viktor; Dolgov, Sergei; Heinmaa, Ivo; Medvid, Artur Physica Status Solidi (C) Current Topics in Solid State Physics 2016 / p. 790 - 792 https://doi.org/10.1002/pssc.201600051 Journal metrics at Scopus Article at Scopus Article at WOS

Влияние неоднородностей в моно- и поликристаллическом Cds на фотоэлектрические и длинновременные неравновесные свойства
Kropman, Daniel; **Lott, Kalju**; Šeinkman, M. Физика, химия и технические применения полупроводников A2B6 : тезисы докладов IV всесоюзного совещания (Одесса, 16-19 ноября 1976 г.) 1976 / с. 123 https://www.ester.ee/record=b2969209*est

Влияние облучения низкоэнергетическими электронами в растровом электронном микроскопе на параметры полупроводниковых приборов
Meiler, Boriss; **Kropman, Daniel**; **Levtšenkova, Alla** Микроэлектроника 1987 / с. 165-169 : илл
https://www.ester.ee/record=b2147720*est

Исследование температурного тушения фотопроводимости в пленках CdS
Kropman, Daniel Полупроводниковые материалы. 1 1969 / с. 107-113 : илл https://www.ester.ee/record=b1346474*est
https://digikogu.taltech.ee/et/Item/da24f532-932d-41c5-8925-a52dfa4b18c8/

Исследование термостимулированной провидимости и эффекта Холла в пленках CdS
Kropman, Daniel Полупроводниковые материалы. 1 1969 / с. 97-105 : илл https://www.ester.ee/record=b1346474*est
https://digikogu.taltech.ee/et/Item/da24f532-932d-41c5-8925-a52dfa4b18c8/

Исследование уровней прилипания в пленках сульфида кадмия
Kropman, Daniel Сборник статей по химии и химической технологии. 19 1968 / с. 87-92 : илл
https://www.ester.ee/record=b2182213*est https://digikogu.taltech.ee/et/Item/026f8881-5a73-4588-acba-0b1ffe988b0f